

ABSTRACT OF THE DISCLOSURE

[0052] A chemical mechanical polishing method is disclosed in which a batch of wafers is first supplied to a low-selectivity, first CMP tool for partly polishing the batch with one or more relatively non-selective CMP slurries (e.g., silica (SiO_2) based); and in which the batch of partly-polished wafers is subsequently transferred to a higher-selectivity, second CMP tool which uses one or more comparatively more-selective CMP slurries (e.g., ceria (CeO_2) based) to further the polishing of the batch of partly-polished wafers and/or to complete the polishing of the partly-polished wafers.
